
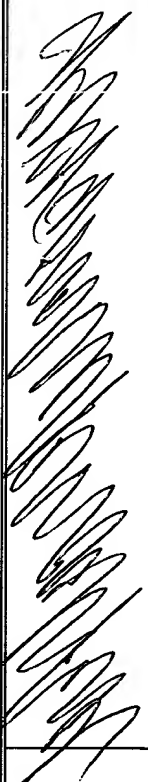

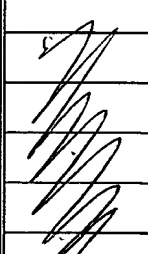
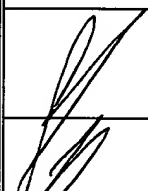





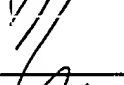



<b>FORM PTO-1449</b> U.S. Department of Commerce Patent and Trademark Office				Attorney Docket Number 5308-168		Serial No. 09/878,442	
<b>LIST OF DOCUMENTS CITED BY APPLICANT</b> (Use several sheets if necessary)							
				Applicants: Das et al.			
				Filing Date: June 12, 2001		Group 2811	
<b>U. S. PATENT DOCUMENTS</b>							
Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
	1	3,924,024	12/2/75	Naber et al.	427	95	
	2	4,466,172	08/21/84	Batra	29	571	
	3	4,875,083	10/17/89	Palmour	357	23.6	
	4	5,170,455	12/8/92	Goossen et al.	385	89	
	5	5,184,199	2/2/93	Fujii et al.	257	77	
	6	5,506,421	4/9/96	Palmour	257	77	
	7	5,510,630	4/23/96	Agarwal et al.	257	77	
	8	5,726,463	3/10/98	Brown et al.	257	77	
	9	5,763,905	6/9/98	Harris	257	77	
	10	5,837,572	11/17/98	Gardner et al.	438	199	
	11	6,025,608	2/15/00	Harris et al.	257	77	
	12	6,100,169	8/8/00	Suvorov et al.	438	519	
	13	6,107,142	8/22/00	Suvorov et al.	438	285	
	14	6,238,967 B1	5/29/01	Shiho et al.	438	244	
	15	6,246,076	6/12/01	Lipkin et al.	257	77	
<b>FOREIGN PATENT DOCUMENTS</b>							
		Document Number	Date	Country	Class	Subclass	Translation Yes   No
	16	0 637 069 A1	2/1/95	EPO			
	17	0 637 069 B1	2/1/95	EPO			
	18	WO 97/17730 *	5/15/97	PCT			
	19	WO 97/39485 *	10/23/97	PCT			
<b>OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)</b>							
	20	Agarwal et al. "A Critical Look at the Performance Advantages and Limitations of 4H-SiC Power UMOSFET Structures," <i>Proceedings of the International Symposium on Power Semiconductor Devices and IC's</i> . (1996) pp. 119-22.					
	21	Agarwal et al. "Temperature Dependence of Fowler-Nordheim Current in 6H- and 4H-SiC MOS Capacitors," <i>IEEE Electron Device Letters</i> . (December 1997) Vol. 18, No. 12, pp. 592-4.					

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Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<b>FORM PTO-1449</b> U.S. Department of Commerce Patent and Trademark Office  LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary) 		Attorney Docket Number 5308-168	Serial No. 09/878,442
		Applicants: Das et al.	
		Filing Date: June 12, 2001	Group 2811
	22	Kobayashi et al. "Dielectric Breakdown and Current Conduction of Oxide/Nitride/Oxide Multi-Layer Structures," 1990 Symposium on VLSI Technology," <i>IEEE</i> , pp. 119-20. 	
	23	Lipkin et al. "Insulator Investigation on SiC for Improved Reliability," <i>IEE Transactions on Electron Devices</i> . (March 1999) Vol. 46, No. 3, pp. 525-32.	
	24	Ma et al. "Fixed and trapped charges at oxide-nitride-oxide heterostructure interfaces formed by remote plasma enhanced chemical vapor deposition," <i>J. Vac. Sci. Technol. B</i> . (Jul/Aug 1993) Vol. 11, No. 4, pp. 1533-40.	
	25	Lipkin, Lori A. U.S. Patent Application entitled, "Method of N <sub>2</sub> O Annealing an Oxide Layer on a Silicon Carbide Layer." Filed April 12, 2001, Serial No. 09/834,283.	
	26	Slater et al. U.S. Patent Application entitled, "Silicon Carbide CMOS Devices." Filed April 15, 1996, Serial No.: 08/631,926	